HSB2836

Silicon Epitaxial Planar Diode for High Speed Switching

HITACHI

ADE-208-485(Z)
Rev 0

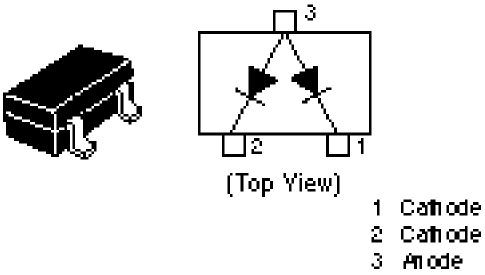
Features

- Fast recovery time.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSB2836	A4	CMPAK

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Peak forward current	I_{FM}[*1]	300	mA
Non-Repetitive peak forward surge current	I_{FSM}[*2]	4	A
Average rectified current	I_O[*1]	100	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Notes: 1. Two device total.
2. Value at duration of 1µsec, two device total.

Electrical Characteristics (Ta = 25°C) *[1]

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	—	—	1.0	V	I_F = 10 mA
	V_{F2}	—	—	1.0		I_F = 50 mA
	V_{F3}	—	—	1.2		I_F = 100 mA
Reverse current	I_R	—	—	0.1	µA	V_R = 80V
Capacitance	C	—	—	4.0	pF	V_R = 0V, f = 1 MHz
Reverse recovery time	t_{rr}	—	—	20	ns	I_F = 10 mA, V_R = 6V, R_L = 50Ω

Note: 1. Per one device.

Main Characteristic

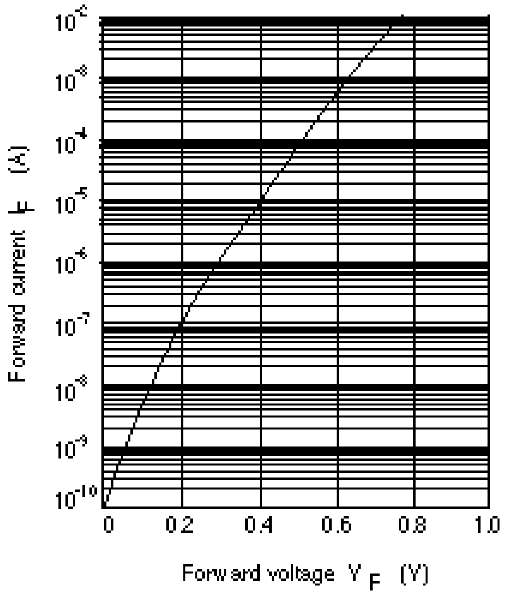


Fig.1 Forward current Vs. Forward voltage

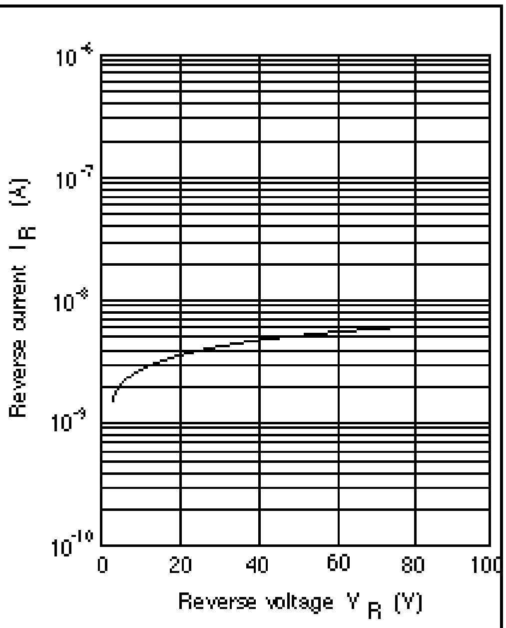


Fig.2 Reverse current Vs. Reverse voltage

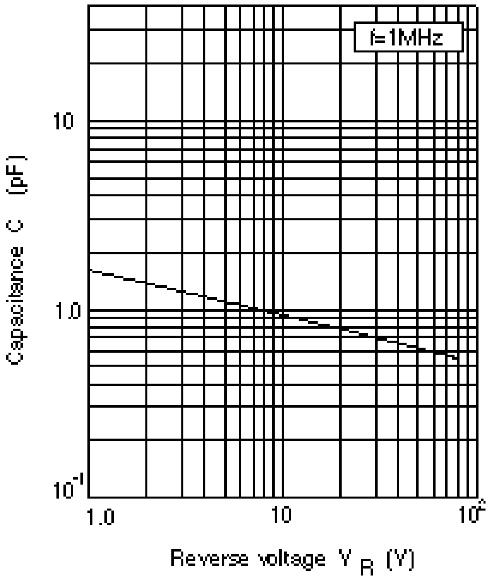
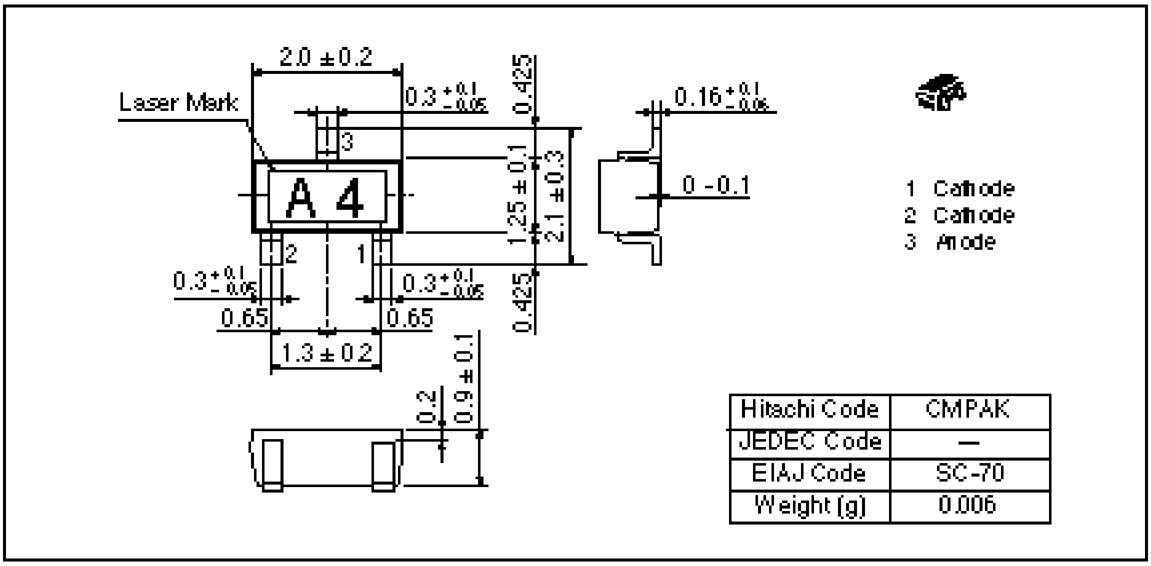


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit : mm



Hitachi Code	CMPAK
JEDEC Code	—
EIAJ Code	SC-70
Weight (g)	0.006